ANMI085089-P34

X-band matched GaN power amplifier module

Features:

Frequency: 8.5~8.9GHz

1dB Output Power: P_{1dB}≥34dBm

PowerGain: Gain=17dB(type)

Efficiency: η=20%(type)

Port Matching: Z_{in}/Z_{out}=50Ω

Description:

ANMI085089-P34 is an internal matching GaN power amplifier module, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 8.5~8.9GHz. This device can be used in different RF/Microwave system and subsystem.The high output power level, high efficiency and wide operating temperature range can make application very flexible.

Maximun Ratings (TC=25℃, Not recommended working under this condition):

	Symbol	Value	Unit
Voltage between source and drain	V_{DS}	40	V
Voltage between gate and source	V_{GS}	-5	V
Storage Temperature Range	T_{stg}	-65 to +175	℃
Drain and Source Channel Temperature	T_{ch}	175	℃

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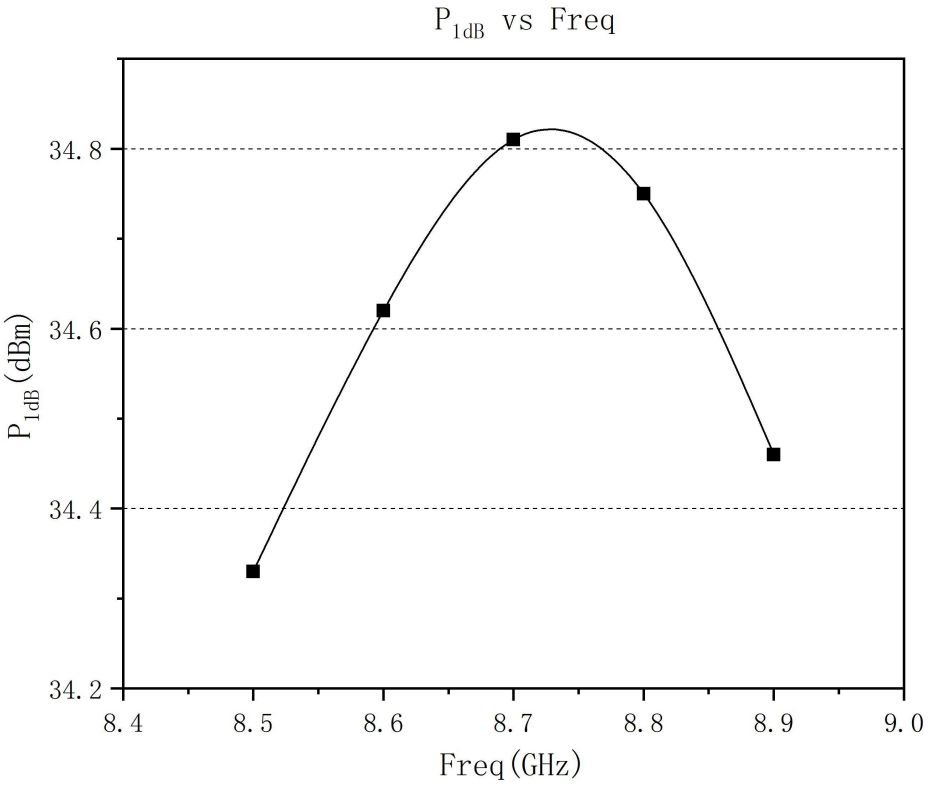
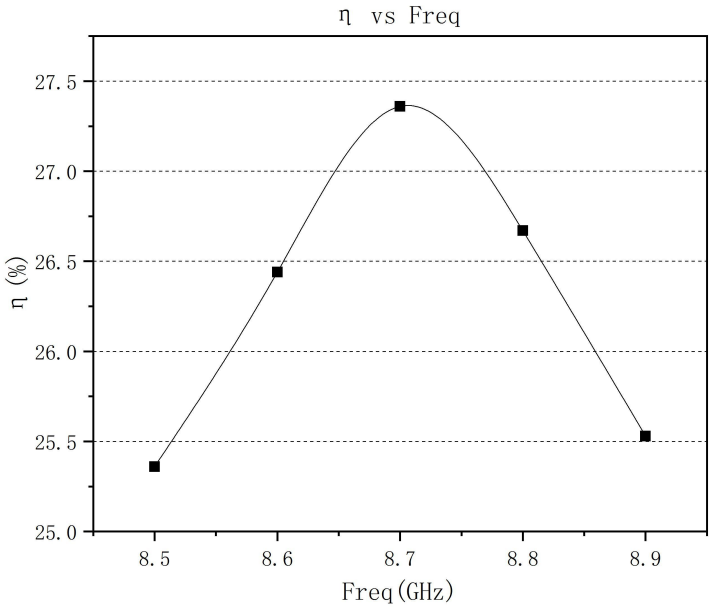
Electrical Characteristics:

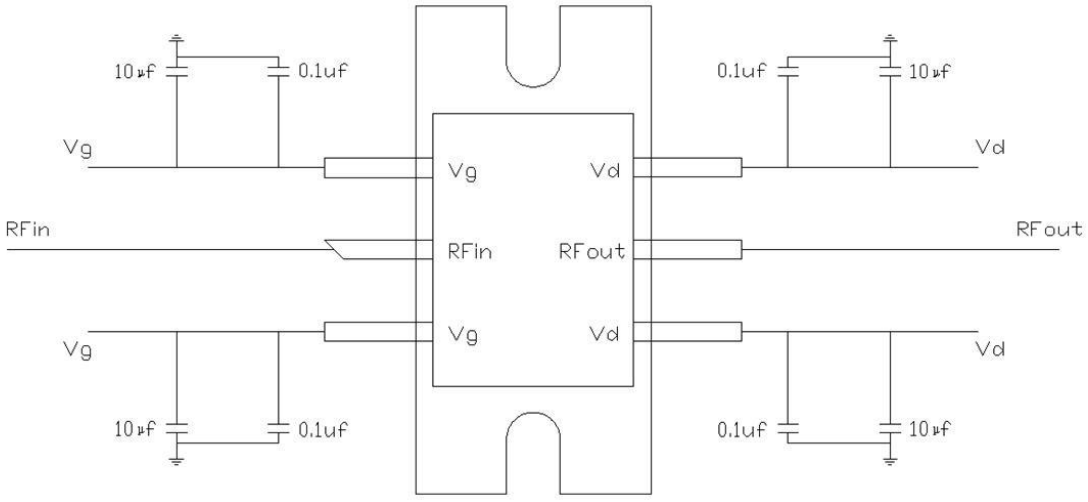
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I_{dsr}	Vds=28V CW. Pin: 17dBm Freq: 8.5~8.9GHz	-	0.4	-	A
1dB Output Power	P_{1dB}		34	-	-	dBm
Gain	G_p		-	17	-	dB
Efficiency	η		-	20	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





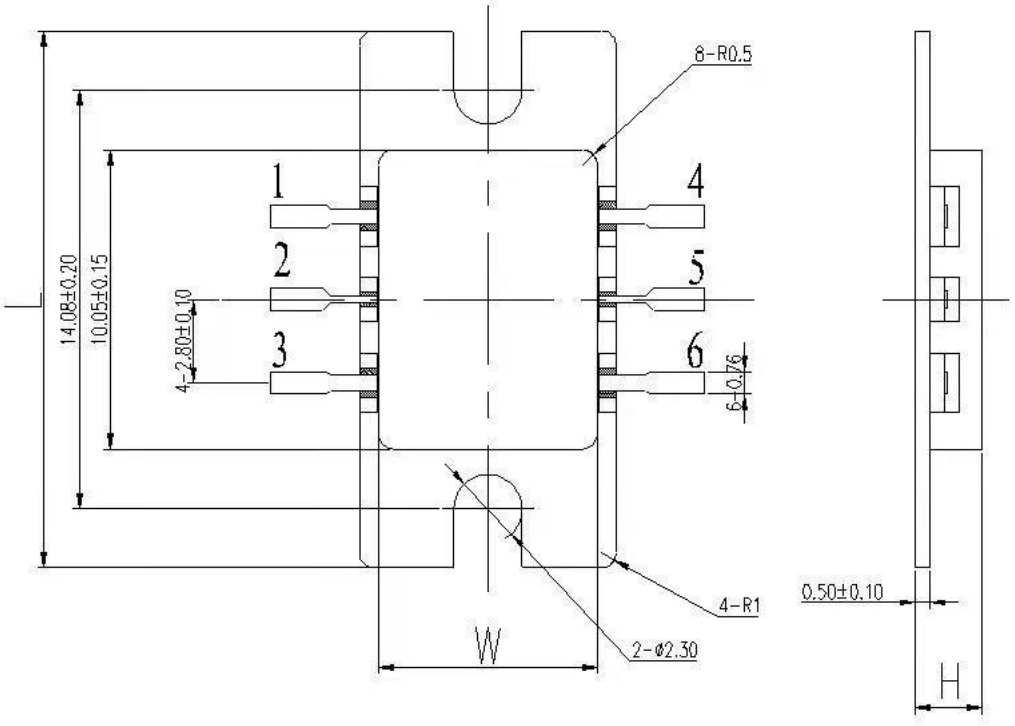
Application Circuit:



ESD Level:

ESD	Class III	2000V

Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly，and wear grounding anti-static bracelet.
- When powering up，first apply grid power then add leakage.